

Vishay Siliconix

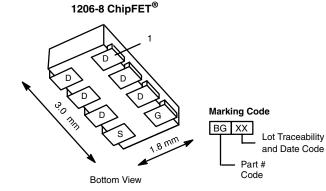
P-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	R_{DS(on)} (Ω)	I _D (A)		
- 20	0.076 at V _{GS} = - 4.5 V	- 4.8		
	0.110 at V _{GS} = - 2.5 V	- 4.0		
	0.160 at V _{GS} = - 1.8 V	- 3.3		

FEATURES

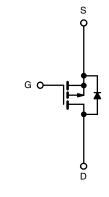
- Halogen-free According to IEC 61249-2-21
 Available
- TrenchFET[®] Power MOSFETs: 1.8 V Rated





Ordering Information: Si5447DC-T1-E3 (Lead (Pb)-free)

Si5447DC-T1-GE3 (Lead (Pb)-free and Halogen-free)



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T_{μ}	_λ = 25 °C, unle	ss otherwise r	noted			
Parameter		Symbol	5 s	Steady State	Unit	
Drain-Source Voltage		V _{DS}	- 20		V	
Gate-Source Voltage		V _{GS}	± 8			
	T _A = 25 °C	– I _D	- 4.8	- 3.5		
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 85 °C		- 3.5	- 2.5	•	
Pulsed Drain Current		I _{DM}	- 15		A	
Continuous Source Current ^a		۱ _S	- 2.1	- 1.1		
	T _A = 25 °C	P _D	2.5	1.3	W	
Maximum Power Dissipation ^a	T _A = 85 °C		1.3	0.7	vv	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C	
Soldering Recommendations (Peak Temperature) ^{b, c}			260		U	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
	t ≤ 5 s	- R _{thJA} R _{thJF}	43	50	
Maximum Junction-to-Ambient ^a	Steady State		83	95	°C/W
Maximum Junction-to-Foot (Drain)	Steady State		14	20	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

b. See Reliability Manual for profile. The ChipFET is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

c. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

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Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \ \mu A$	- 0.45			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, \text{ V}_{GS} = \pm 8 \text{ V}$			± 100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 16 V, V _{GS} = 0 V			- 1	μA	
		V_{DS} = - 16 V, V_{GS} = 0 V, T_{J} = 85 °C			- 5		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \leq$ - 5 V, V_{GS} = - 4.5 V	- 15			Α	
Drain-Source On-State Resistance ^a		V _{GS} = - 4.5 V, I _D = - 3.5 A		0.064	0.076		
	R _{DS(on)}	V _{GS} = - 2.5 V, I _D = - 2.9 A	0.091	0.110	Ω		
		V _{GS} = - 1.8 V, I _D = - 1 A		0.130	0.160	1	
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 10 V, I _D = - 3.5 A		9		S	
Diode Forward Voltage ^a	V _{SD}	I _S = - 1.1 A, V _{GS} = 0 V		- 0.8	- 1.2	V	
Dynamic ^b							
Total Gate Charge	Qg			6.5	10	nC	
Gate-Source Charge	Q _{gs}	V_{DS} = - 10 V, V_{GS} = - 4.5 V, I_{D} = - 3.5 A		1.4			
Gate-Drain Charge	Q _{gd}			1.3		1	
Turn-On Delay Time	t _{d(on)}			14	21		
Rise Time	t _r	V_{DD} = - 10 V, R_L = 10 Ω		29	45	ns	
Turn-Off Delay Time	t _{d(off)}	$\text{I}_\text{D}\cong$ - 1 A, V_GEN = - 4.5 V, R_G = 6 Ω		42	65		
Fall Time	t _f			35	55		
Source-Drain Reverse Recovery Time	t _{rr}	I _F = - 1.1 A, dl/dt = 100 A/μs		30	60		

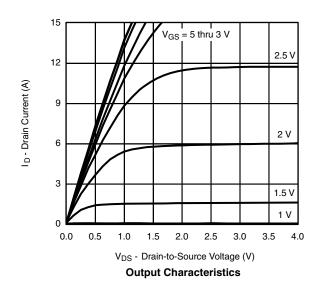
Notes:

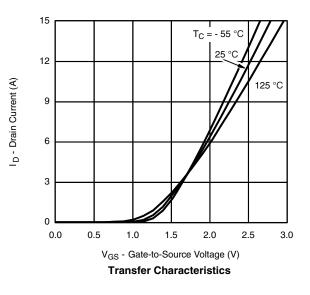
a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



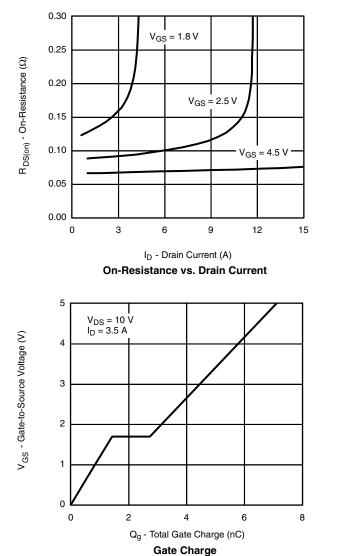


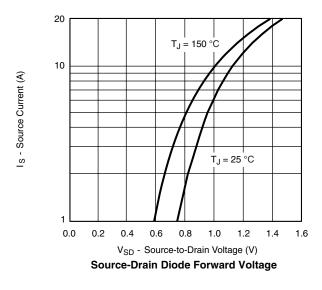


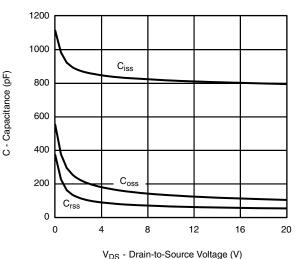
Si5447DC

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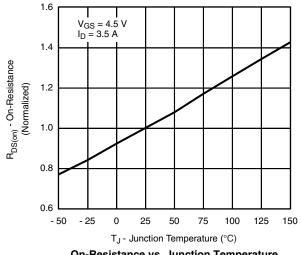
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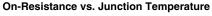


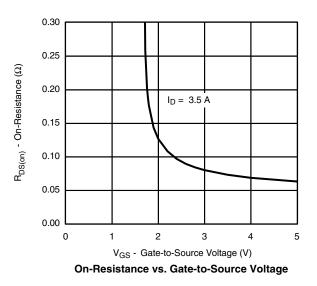




Capacitance

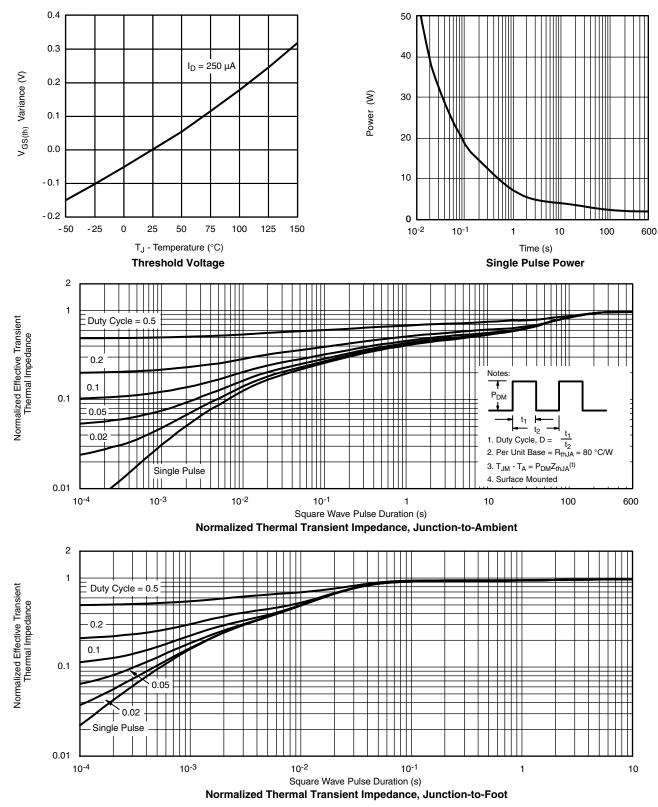






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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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